

HSM2693A

Silicon Epitaxial Planar Diode for Tuner Band Switch

HITACHI

Preliminary
Rev. 2
Jun. 1993

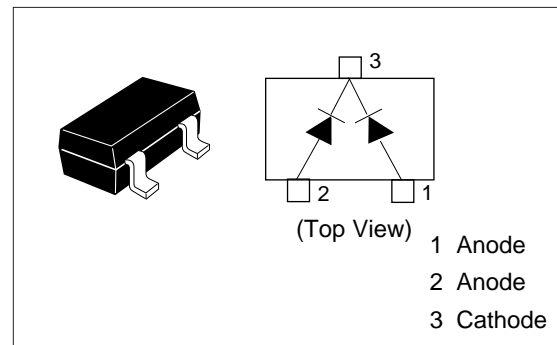
Features

- Low forward resistance. ($r_f=0.9\Omega$ max)
- Low capacitance. ($C=1.2\text{pF}$ max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM2693A	B 4	MPAK

Pin Arrangement



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Power dissipation	p_d^*	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-45 to +125	$^\circ\text{C}$
Operation temperature	T_{opr}	-20 to +60	$^\circ\text{C}$

* Two device total

Electrical Characteristics ($T_a = 25^\circ\text{C}$) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	35	—	—	V	$I_R = 10 \mu\text{A}$
Reverse current	I_R	—	—	50	nA	$V_R = 25 \text{V}$
Forward voltage	V_F	—	—	1.0	V	$I_F = 10 \text{mA}$
Capacitance	C	—	—	1.2	pF	$V_R = 6 \text{V}, f = 1 \text{MHz}$
Forward resistance	r_f	—	—	0.9	Ω	$I_F = 2 \text{mA}, f = 100 \text{MHz}$

* Per one device

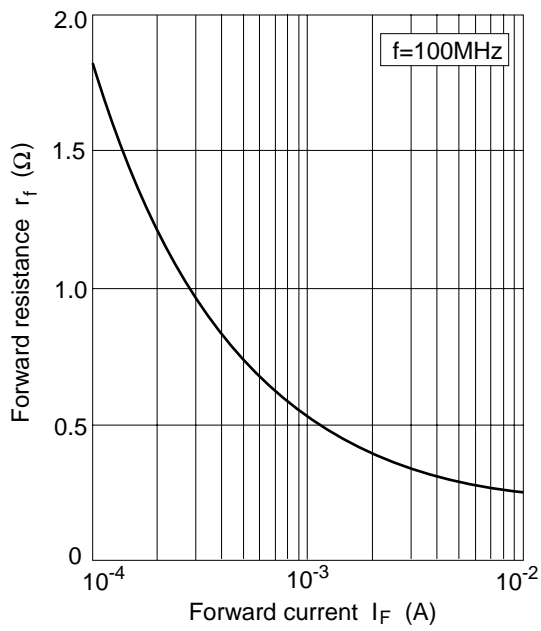


Fig.1 Forward resistance Vs. Forward current

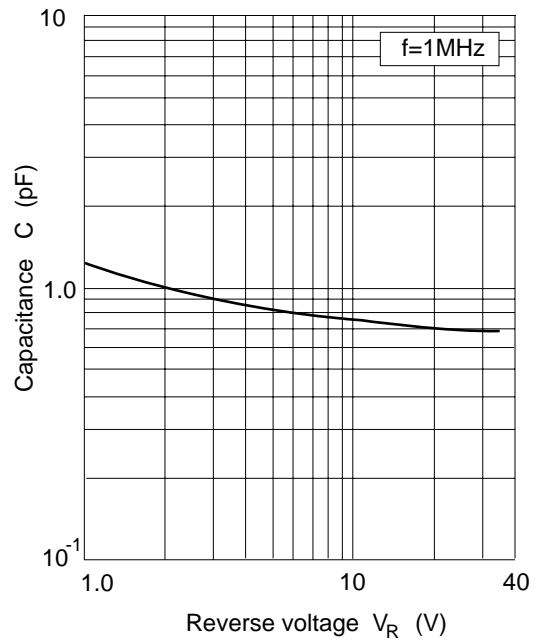


Fig.2 Capacitance Vs. Reverse voltage

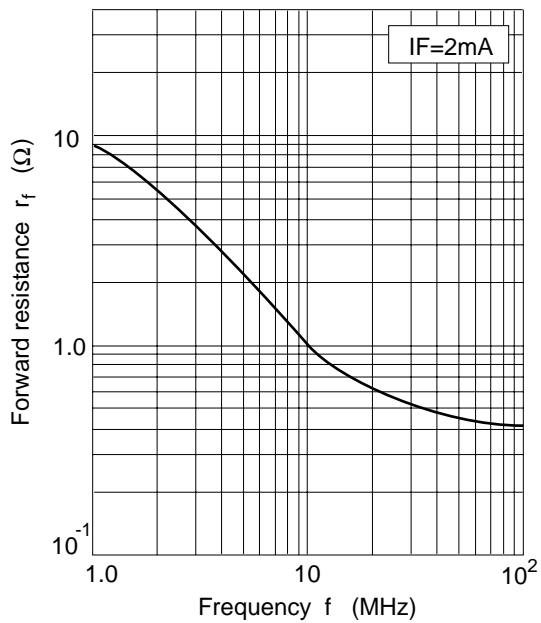


Fig.3 Forward resistance Vs. Frequency

Package Dimensions

Unit: mm

